

Notice of References CitedApplication/Control No.
09/755,673Applicant(s)/Patent Under
Reexamination
FORBES ET AL.Examiner
Khiem D NguyenArt Unit
2823

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,886,364	03-1999	Zhang, Hongyong	257/53
	B	US-6,150,209	11-2000	Sun et al.	438/240
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Choi et al. JP 2000013654 DRAM capacitor manufacturing method involves forming compound dielectric film comprising alumina layer and aluminum nitride layer, between upper and lower electrodes (August 12, 1998).
	V	Chiu et al. TW 381343 Method for preventing dielectric cracking of capacitors by employing spacer structure to cover the shape corner at the bottom of stacked capacitor sidewall (August 4, 1998).
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.